



ALPHA & OMEGA
SEMICONDUCTOR

AO4419

P-Channel Enhancement Mode Field Effect Transistor



General Description

The AO4419 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO4419 is Pb-free (meets ROHS & Sony 259 specifications). AO4419L is a Green Product ordering option. AO4419 and AO4419L are electrically identical.*

Features

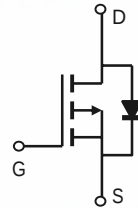
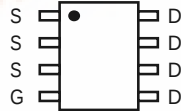
$V_{DS} (V) = -30V$

$I_D = -9.7 A (V_{GS} = -10V)$

$R_{DS(ON)} < 20m\Omega (V_{GS} = -10V)$

$R_{DS(ON)} < 35m\Omega (V_{GS} = -4.5V)$

SOIC-8
Top View



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$ -9.7	A
		$T_A=70^\circ C$ -8.1	
Pulsed Drain Current ^B	I_{DM}	-40	A
Power Dissipation ^A	P_D	$T_A=25^\circ C$ 3	W
		$T_A=70^\circ C$ 2.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A		63	75	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	21	30	$^\circ C/W$



Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.4	-2	-2.7	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-40			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-9.7A		16	20	mΩ
		T _J =125°C		20.9	26	
		V _{GS} =-4.5V, I _D =-7A		26	35	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-9.7A		21.7		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Maximum Body-Diode Continuous Current				-1.2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		1573	1900	pF
C _{oss}	Output Capacitance			319		pF
C _{rss}	Reverse Transfer Capacitance			211		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		6.7	8	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-15V, I _D =-9.7A		26.4	32	nC
Q _g (4.5V)	Total Gate Charge (4.5V)			13.7	17	nC
Q _{gs}	Gate Source Charge			3.8		nC
Q _{gd}	Gate Drain Charge			6.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =1.5Ω, R _{GEN} =3Ω		9.5		ns
t _r	Turn-On Rise Time			8		ns
t _{D(off)}	Turn-Off DelayTime			44.2		ns
t _f	Turn-Off Fall Time			22.2		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-9.7A, dI/dt=100A/μs		25.2	31	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-9.7A, dI/dt=100A/μs		14.1		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

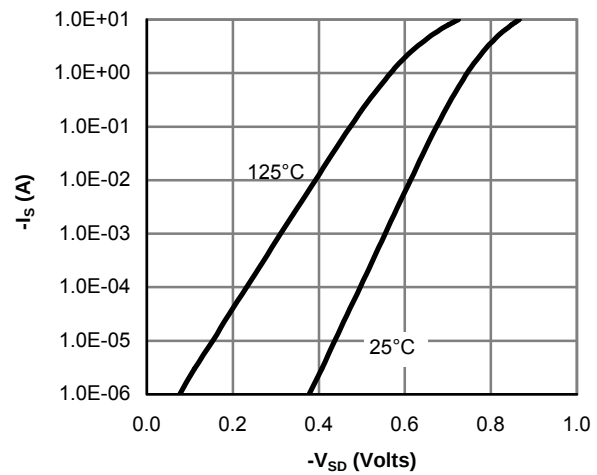
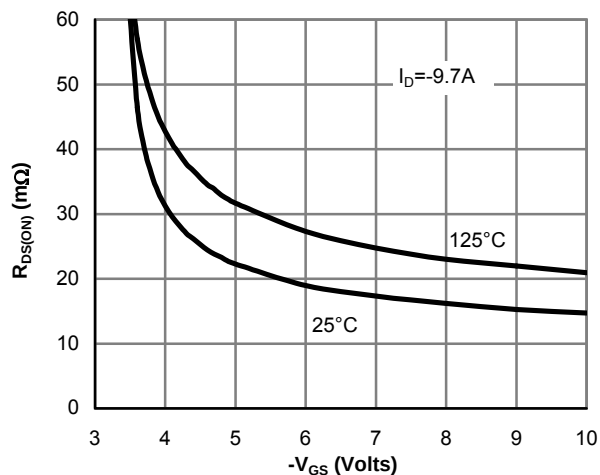
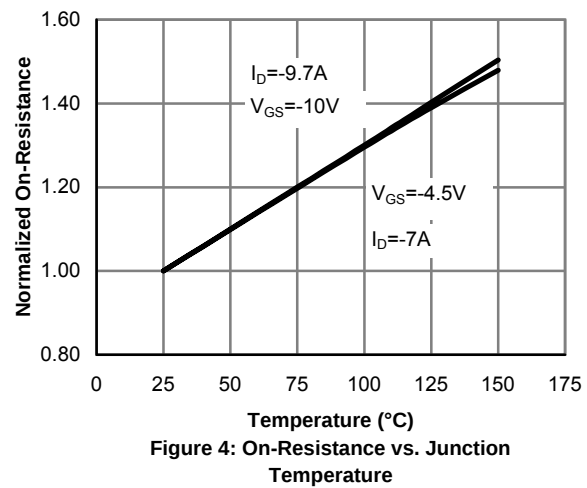
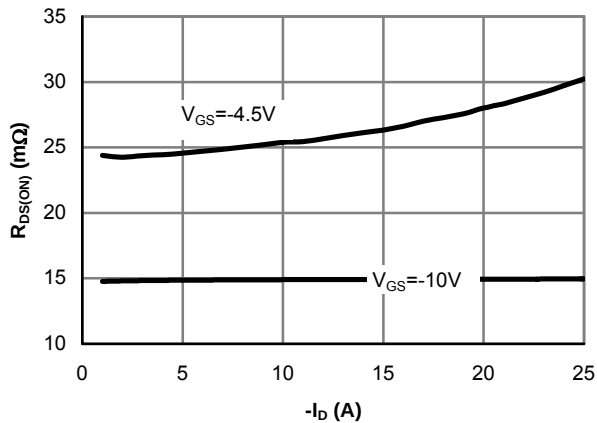
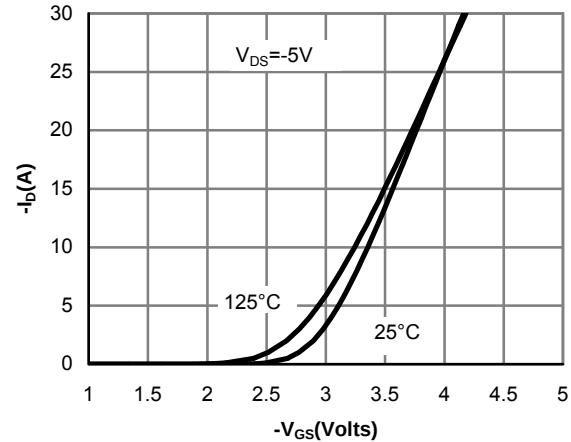
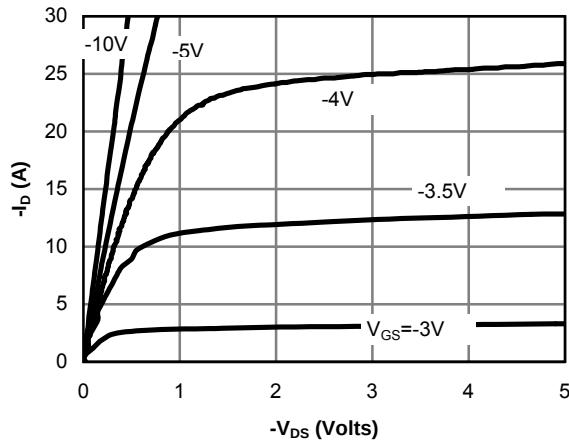
D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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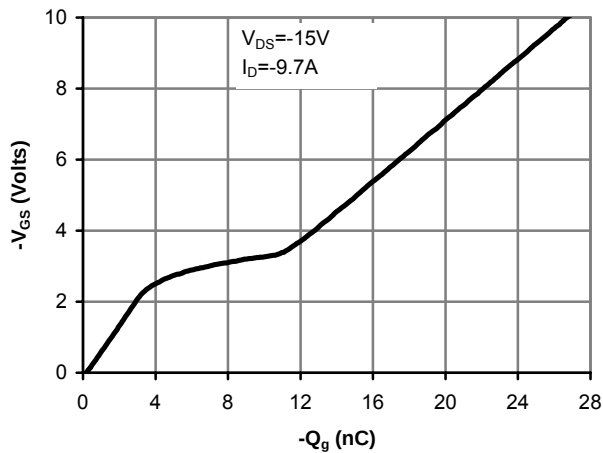


Figure 7: Gate-Charge Characteristics

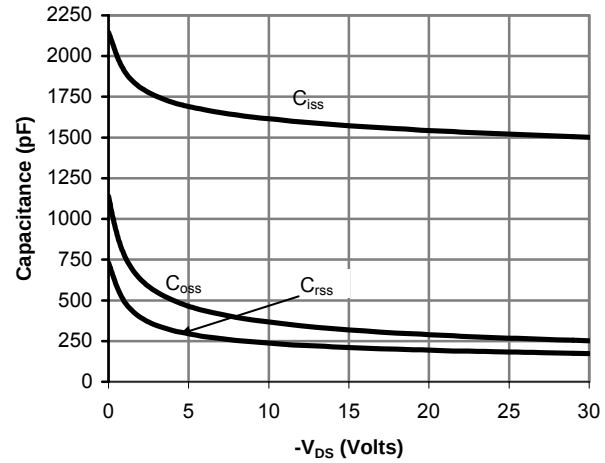


Figure 8: Capacitance Characteristics

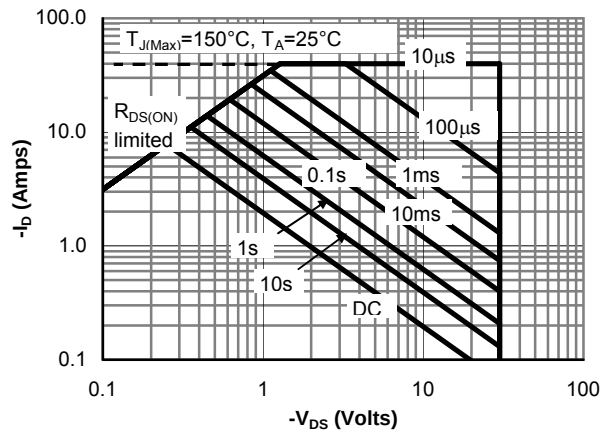


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

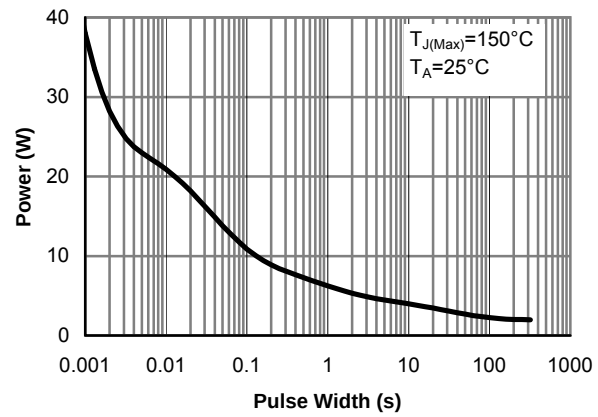


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

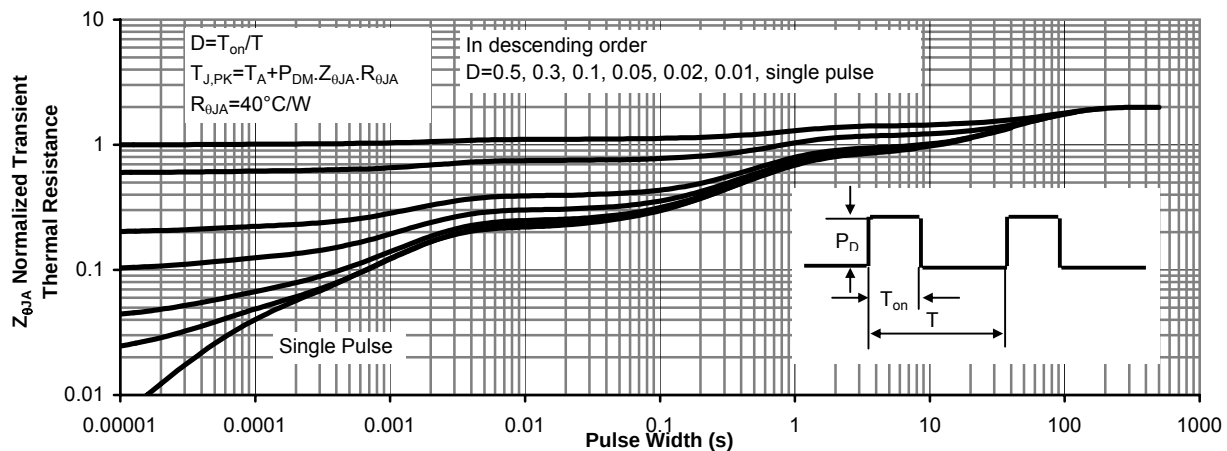


Figure 11: Normalized Maximum Transient Thermal Impedance